

**SPECIFICATION OF LED CHIP**  
**CN810-40P**  
**[INFRARED]**

1) Commodity Type and Physical Characteristics.

- |                      |                     |                  |            |
|----------------------|---------------------|------------------|------------|
| 1. Material          | GaAlAs/GaAlAs (DDH) |                  |            |
| 2. Electrode         | Top Side            | P (anode) side   | : Au Alloy |
|                      | Bottom Side         | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1               |                  |            |
| 4. Chip Size         | Fig.2               |                  |            |
| 5. Chip Thickness    | Fig.2               |                  |            |
| 6. Emission Area     | Fig.2               |                  |            |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.40	1.60	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	3.0	5.0		mW
Peak Wavelength	$\lambda_P$	If=20mA	800	810	820	nm
Spectral FWHM	$\Delta\lambda$	If=20mA		40		nm
RiseTime	tr	If=20mA		25		ns
FallTime	tf	If=20mA		15		ns

‡ Die shall be mounted on TO-18 gold header without resin coated.(Ta=25°C)

[Unit: um]

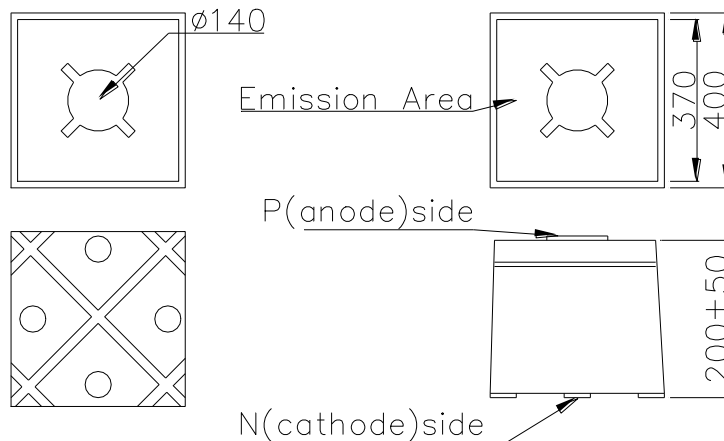


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area